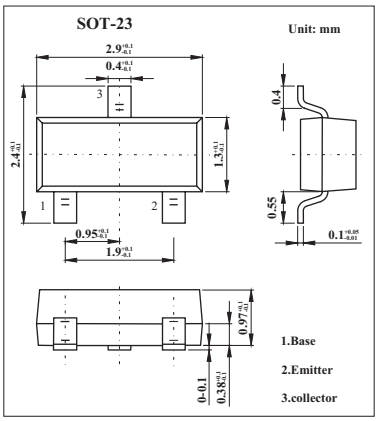
NPN General Purpose Transistors

BCX20



■ Features

● General Purpose Transistors.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V_{CES}	30	V
Collector-emitter voltage	V_{CEO}	25	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	800	A
Collector dissipation	Pc	310	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-65 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Max	Unit
Collector-emitter breakdown voltage	BV_{CEO}	I_C = 10mA, I_B = 0	25		V
Collector-emitter breakdown voltage	BV_{CES}	I_C = 100μA, V_{BE} = 0	30		V
Emitter-base breakdown voltage	BV_{EBO}	I_E = 10μA, I_C = 0	5		V
Collector cut-off current	I_{CBO}	V_{CE} = 20V, V_{BE} = 0		100	nA
Emitter-base cut-off current	I_{EBO}	V_{BE} =5V, I_C = 0		10	nA
DC current gain	h_{FE}	V_{CE} = 1V, I_C = 100mA	100	600	
		V_{CE} = 1V, I_C = 300mA	70		
		V_{CE} = 1V, I_C = 500mA	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 500mA, I_B = 50mA		0.62	V
Base-emitter saturation voltage	$V_{BE(on)}$	V_{CE} = 1A, I_B = 500mA		1.2	V

■ Marking

Marking	U2